

L Number	Hits	Search Text	DB	Time stamp
3	52	kim-young-soo.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 20:33
-	106	ti same atomic adj layer adj deposition and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 20:32
-	20	ti same atomic adj layer adj deposition and capacitor and bottom adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/26 23:23
-	11	ti same atomic adj layer adj deposition and capacitor and nh\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/26 23:24
-	55	ti same atomic adj layer adj deposition and "nh.sub.3" and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/26 23:26
-	39	ti same atomic adj layer adj deposition and "nh.sub.3" and electrode and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/26 23:28
-	58	ald with tin and "nh.sub.3" and electrode and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/26 23:28
-	5	ald near tin and "nh.sub.3" and electrode and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/26 23:34
-	4	ald near tin and "nh.sub.3" and electrode and capacitor and nitrid\$9 same dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 00:34
-	3	ald near tin and "nh.sub.3" and electrode and capacitor and nitrid\$9 with dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 00:34
-	0	ald near tin and "nh.sub.3" and electrode and capacitor and nitridiz\$6 with dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 00:34
-	0	ald near tin and "nh.sub.3" and nitridiz\$6 with dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 00:34
-	6	ald and "nh.sub.3" and nitridiz\$6 with dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 00:35

-	10	ald with tin and "nh.sub.3" and nitridation same dielectric and tin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 01:13
-	11	ald and "nh.sub.3" and nitridation with dielectric and tin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 01:20
-	11	ald and "nh.sub.3" and (nitridation or nitridify) with dielectric and tin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 01:18
-	779	438/785	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 01:20
-	1074	(438/778).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 01:21
-	272	(438/775).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 01:22
-	13	ald adj tin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 01:22
-	3	ald adj tin and nitridation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 01:23
-	4	ald near tin and nitridation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 01:23
-	32	ald with tin and nitridation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 01:26
-	2	ald with tin and nitridation with dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 01:24
-	20	"6225168"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 01:24
-	3	ald with tin and nitriding with dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 20:30
1	4156	(438/396).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 20:31

2	221	(438/399).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/27 20:31
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